MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

# TPH12008NH

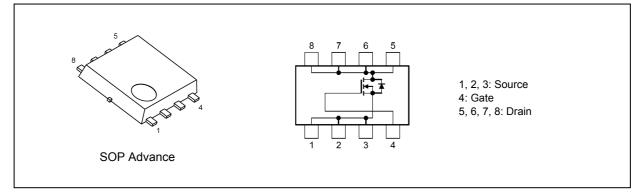
### 1. Applications

- DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

#### 2. Features

- (1) Small, thin package
- (2) High-speed switching
- (3) Small gate charge:  $Q_{SW} = 8.1 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 10.1 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (5) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 80 \ V)$
- (6) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.3 mA)

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics               |                         |                    |                  | Rating     | Unit |
|-------------------------------|-------------------------|--------------------|------------------|------------|------|
| Drain-source voltage          |                         |                    | V <sub>DSS</sub> | 80         | V    |
| Gate-source voltage           |                         |                    | V <sub>GSS</sub> | ±20        |      |
| Drain current (DC)            | (Silicon limit)         | (Note 1), (Note 2) | Ι <sub>D</sub>   | 44         | A    |
| Drain current (DC)            | (T <sub>c</sub> = 25°C) | (Note 1)           | I <sub>D</sub>   | 24         |      |
| Drain current (pulsed)        | (t = 1 ms)              | (Note 1)           | I <sub>DP</sub>  | 97         |      |
| Power dissipation             | (T <sub>c</sub> = 25°C) |                    | PD               | 48         | W    |
| Power dissipation             | (t = 10 s)              | (Note 3)           | PD               | 2.8        | W    |
| Power dissipation             | (t = 10 s)              | (Note 4)           | PD               | 1.6        | W    |
| Single-pulse avalanche energy |                         | (Note 5)           | E <sub>AS</sub>  | 58         | mJ   |
| Avalanche current             |                         |                    | I <sub>AR</sub>  | 24         | A    |
| Channel temperature           |                         |                    | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature           |                         |                    | T <sub>stg</sub> | -55 to 150 | 7    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

#### 5. Thermal Characteristics

| Characteristics                       |                         |          |                       | Max  | Unit |
|---------------------------------------|-------------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance    | (T <sub>c</sub> = 25°C) |          | R <sub>th(ch-c)</sub> | 2.6  | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s)              | (Note 3) | R <sub>th(ch-a)</sub> | 44.6 | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s)              | (Note 4) | R <sub>th(ch-a)</sub> | 78.1 | °C/W |

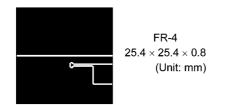
Note 1: Ensure that the channel temperature does not exceed 150°C.

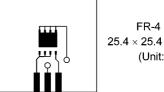
Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V\_DD = 60 V, T\_ch = 25°C (initial), L = 0.086 mH, R\_G = 1.0  $\Omega$ , I<sub>AR</sub> = 24 A





 $25.4\times25.4\times0.8$ (Unit: mm)

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

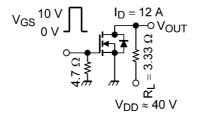
#### 6. Electrical Characteristics

### 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                  | Min | Тур. | Max  | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V                | _   | _    | ±0.1 | μA   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V   | _   |      | 10   |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V   | 80  | —    | —    | V    |
|                                | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V | 60  | _    | _    |      |
| Gate threshold voltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.3 mA | 2.0 | _    | 4.0  |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A   | _   | 10.1 | 12.3 | mΩ   |

## 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max  | Unit |
|--------------------------------|------------------|--|-----|------|------|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 1490 | 1900 | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |  | _   | 16   | 50   |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 330  | _    |      |
| Gate resistance                | rg               |  | _   | 1.1  | 1.7  | Ω    |
| Switching time (rise time)     | t <sub>r</sub>   | See Figure 6.2.1.  | _   | 5.0  | —    | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | _   | 15   | —    |      |
| Switching time (fall time)     | t <sub>f</sub>   |  | _   | 7.4  | _    |      |
| Switching time (turn-off time) | t <sub>off</sub> | ]  |     | 24   |      |      |



Duty  $\leq$  1%, t<sub>w</sub> = 10  $\mu$ s

Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

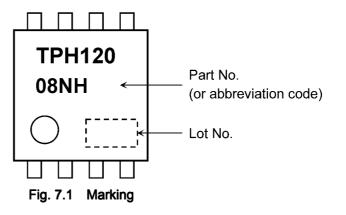
| Characteristics                                    | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus<br>gate-drain) | Qg               | $V_{DD} \approx 40 \text{ V}, \text{ V}_{GS} \text{ = } 10 \text{ V}, \text{ I}_{D} \text{ = } 24 \text{ A}$ | —   | 22   | —   | nC   |
| Gate-source charge 1                               | Q <sub>gs1</sub> |  |     | 7.6  | _   |      |
| Gate-drain charge                                  | Q <sub>gd</sub>  |  | _   | 4.9  | _   |      |
| Gate switch charge                                 | Q <sub>SW</sub>  | ]  | _   | 8.1  | _   |      |

## 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

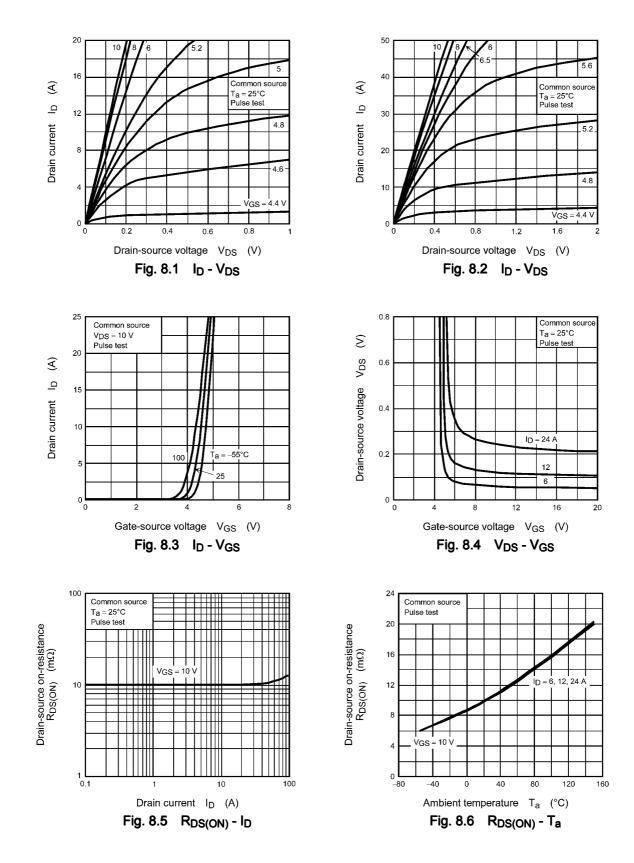
| Characteristics                         | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|---|------------------|---|-----|------|------|------|
| Reverse drain current (pulsed) (Note 6) | I <sub>DRP</sub> | —   | _   | _    | 97   | А    |
| Diode forward voltage                   | V <sub>DSF</sub> | I <sub>DR</sub> = 24 A, V <sub>GS</sub> = 0 V |     | _    | -1.2 | V    |

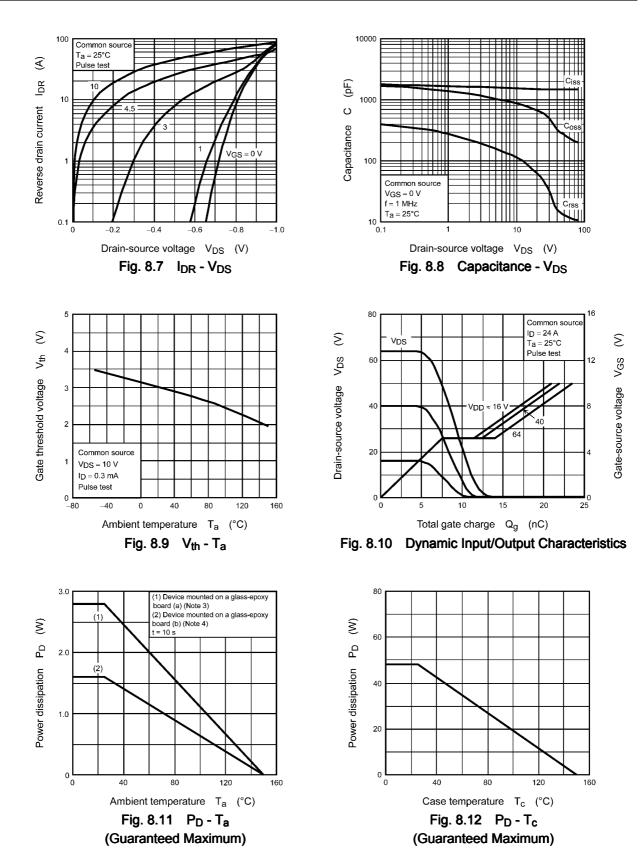
Note 6: Ensure that the channel temperature does not exceed 150°C.

## 7. Marking

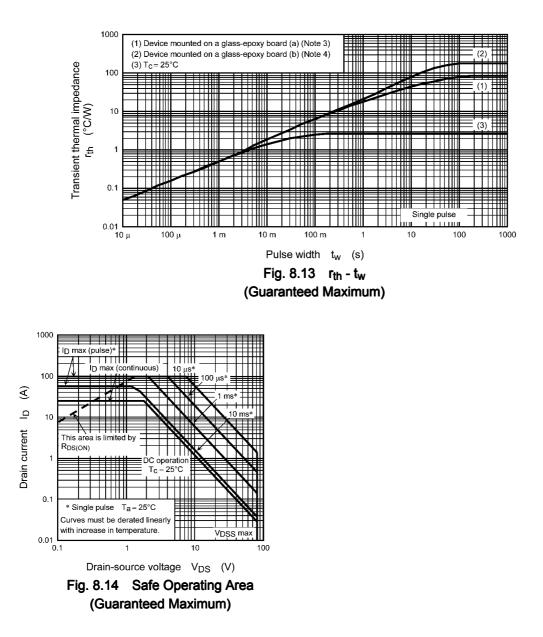


## 8. Characteristics Curves (Note)









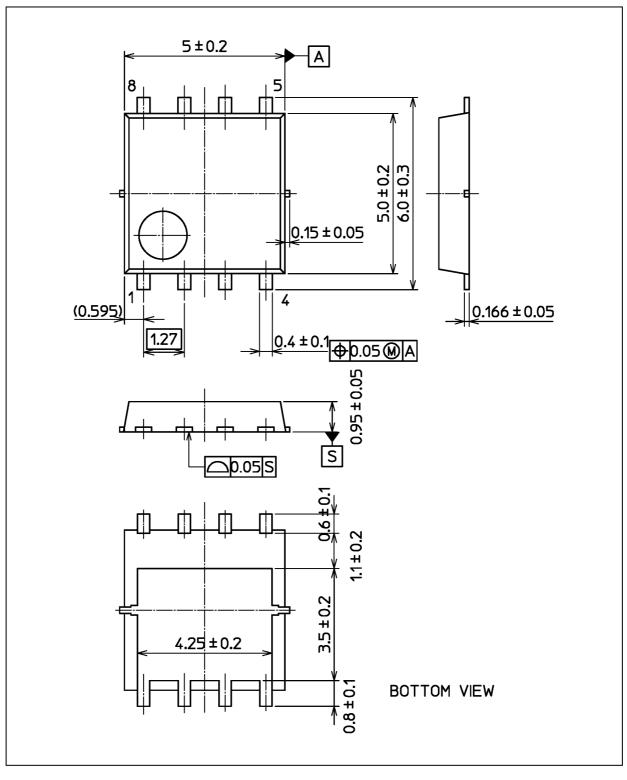
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## TPH12008NH

### Package Dimensions

Unit: mm



Weight: 0.069 g (typ.)

Package Name(s)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

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